Prisemi®

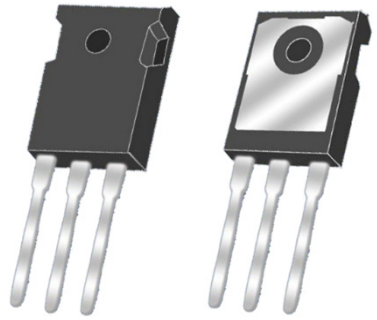
PSJMTAF60R90

N-Channel MOSFET

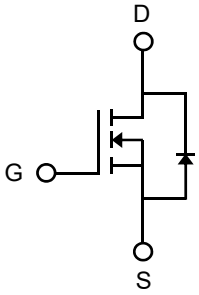
Description

The PSJMTAF60R90 is a high voltage MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

MOSFET Product Summary		
V_{DS}(V)	$R_{DS(on)}$(mΩ)(Typ)	I_D(A)
600	75@ V_{GS} = 10V	38



TO-247-3L



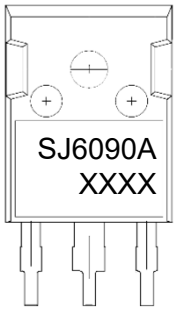
Circuit Diagram

Feature

- High Power and current handing capability
- Lead free product is acquired
- Surface Mount Package

Applications

- PWM applications
- Load switch
- Power management
- DC-DC Converters
- Wireless Chargers



Marking (Top View)

Absolute maximum rating@25℃

Rating		Symbol	Value	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Drain Current-Continuous[1]	T_C=25℃	I_D	38	A
	T_C=100℃		24	
Pulsed Drain Current[2]		I_{DM}	114	A
Total Power Dissipation[3]		P_D	284	W
Avalanche Current[4]		I_{AS}	7.0	A
Avalanche Energy[4]		E_{AS}	1225	mJ
Thermal Resistance , Junction-case[5]		$R_{\theta JC}$	0.44	℃/W
Thermal Resistance Junction-to-Ambient[6]		$R_{\theta JA}$	35	℃/W
Junction and Storage Temperature Range		T_J,T_{STG}	-55~+150	℃

Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V,I_D = 250μA	600	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 600V,V_{GS} = 0V	-	-	10	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±30V,V_{DS} = 0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS},I_D = 250μA	3.0	3.7	5.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} = 10V,I_D = 20A	-	75	90	mΩ
Dynamic Characteristics[7)]						
Input Capacitance	C_{lss}	V_{DS} = 200V,V_{GS} = 0V, f = 100KHz	-	2754	-	pF
Output Capacitance	C_{oss}		-	70	-	
Reverse Transfer Capacitance	C_{rss}		-	2.3	-	
Switching Characteristics[7)]						
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 300V, V_{GS} = 10V, R_G = 10Ω, I_D = 40A	-	29	-	ns
Turn-on Rise Time	t_r		-	35	-	
Turn-Off Delay Time	$t_{d(off)}$		-	80	-	
Turn-Off Fall Time	t_f		-	12	-	
Total Gate Charge	Q_g	V_{DS} = 480V, V_{GS} = 10V, I_D = 40A	-	50	-	nC
Gate-Source Charge	Q_{gs}		-	12	-	
Gate-Drain Charge	Q_{gd}		-	24	-	
Gate Resistance	R_g	f=1MHz, Open Drain	-	2.0	-	Ω
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS} = 0V,I_S = 20A	-	0.7	1.2	V

Notes:
1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. Repetitive Rating: Pulse width limited by maximum junction temperature(T_{J_Max}=150℃).
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. This single-pulse measurement was taken under the following condition [L=50mH,V_{GS}=10V,V_{DS}=50V]while it's value is limited by T_{J_Max}=150℃
5. Device mounted on infinite heatsink
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Guaranteed by design, not subject to production

Typical Characteristics

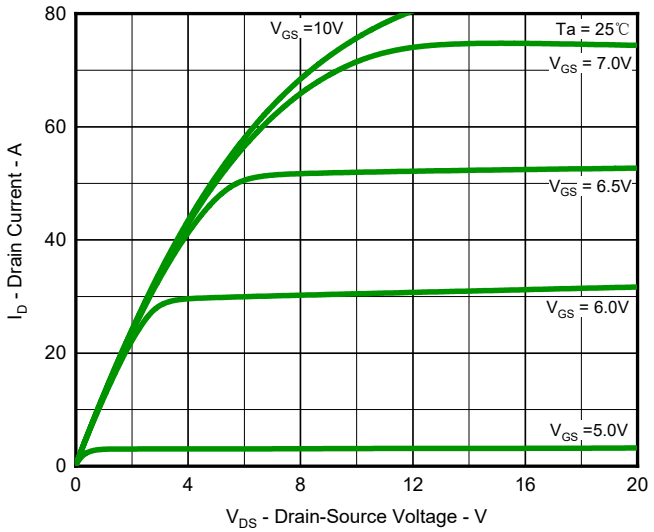


Fig.1 Output Characteristics

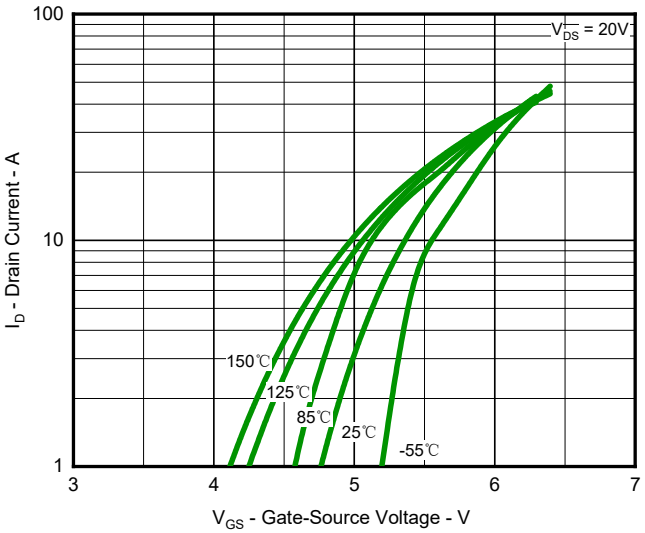


Fig.2 Typical Transfer Characteristic

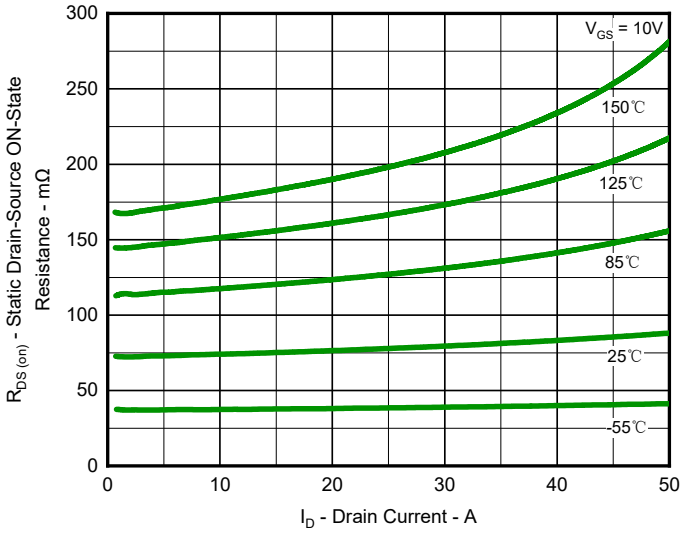


Fig.3 Typical On-Resistance vs Drain Current and Temperature

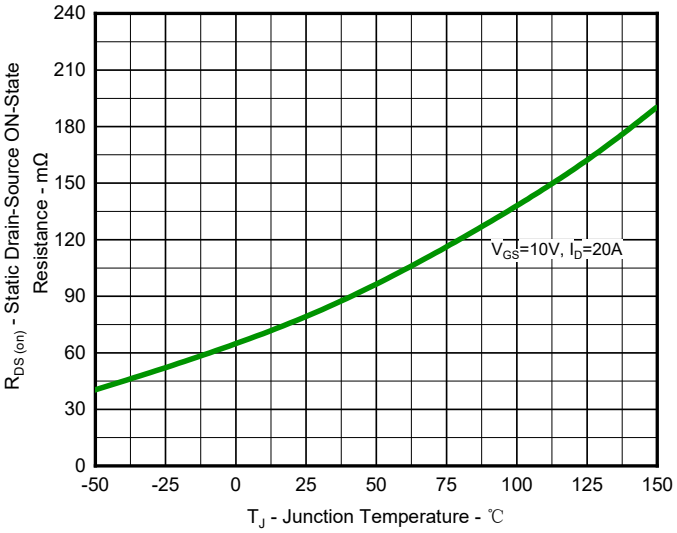


Fig.4 On-Resistance Variation with Temperature

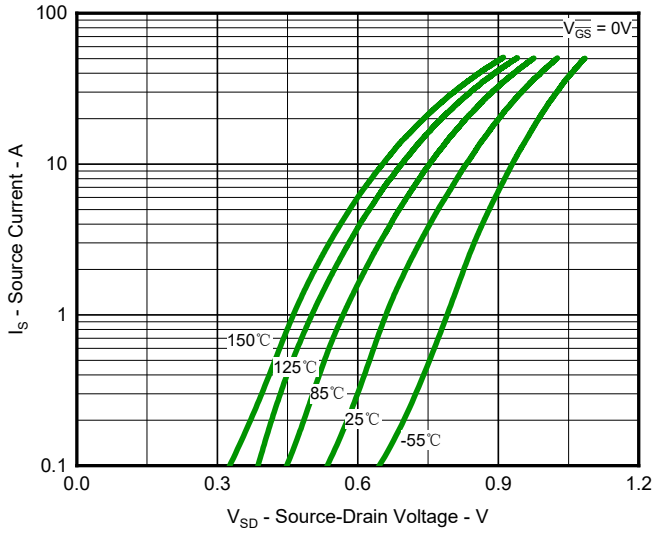


Fig.5 Diode Forward Voltage vs. Current

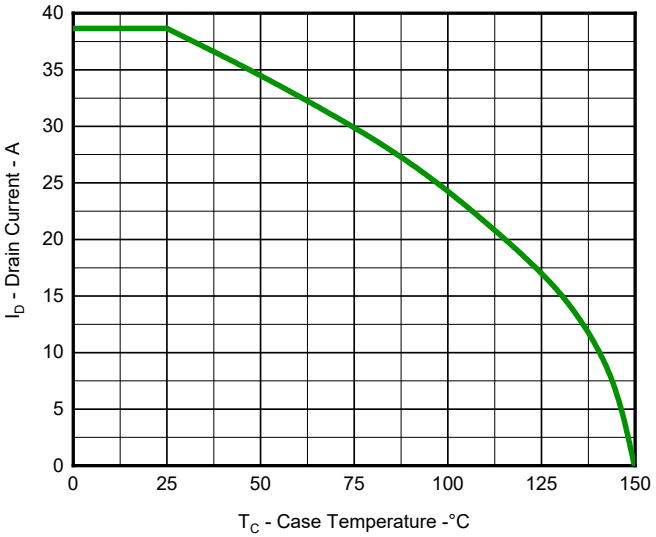


Fig.6 Maximum Drain Current vs. Case Temperature

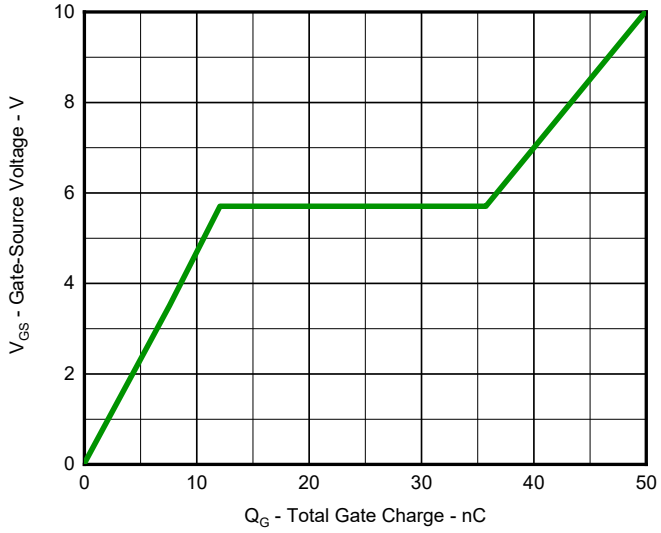


Fig.7 Gate Charge Characteristics

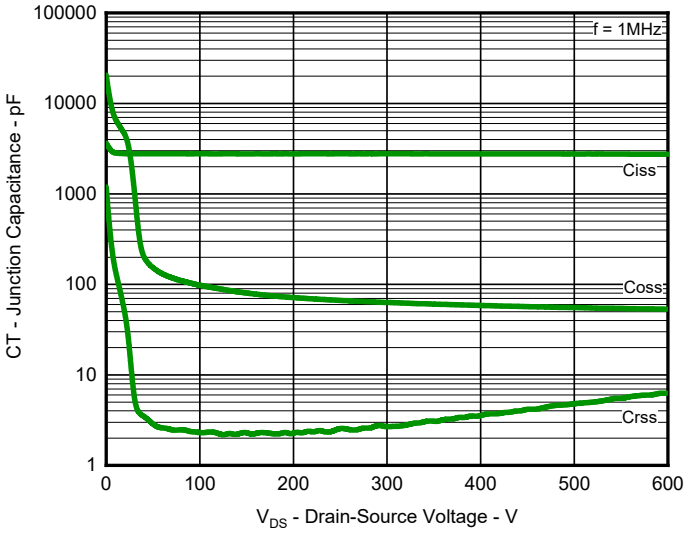


Fig.8 Typical Junction Capacitance

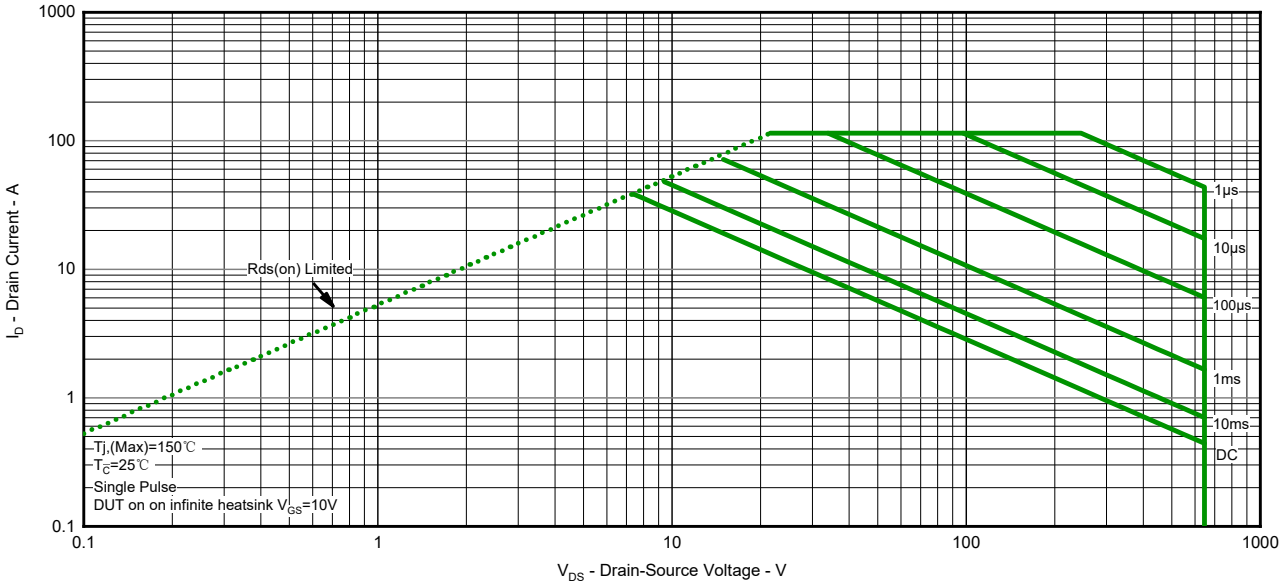


Fig.9 Safe Operation Area

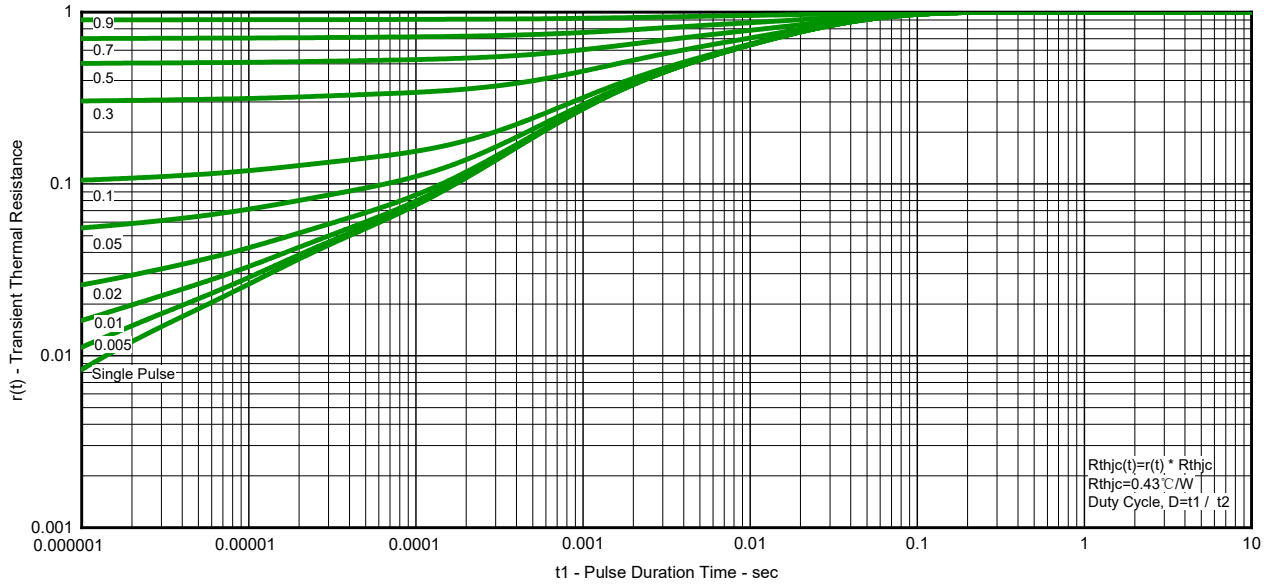
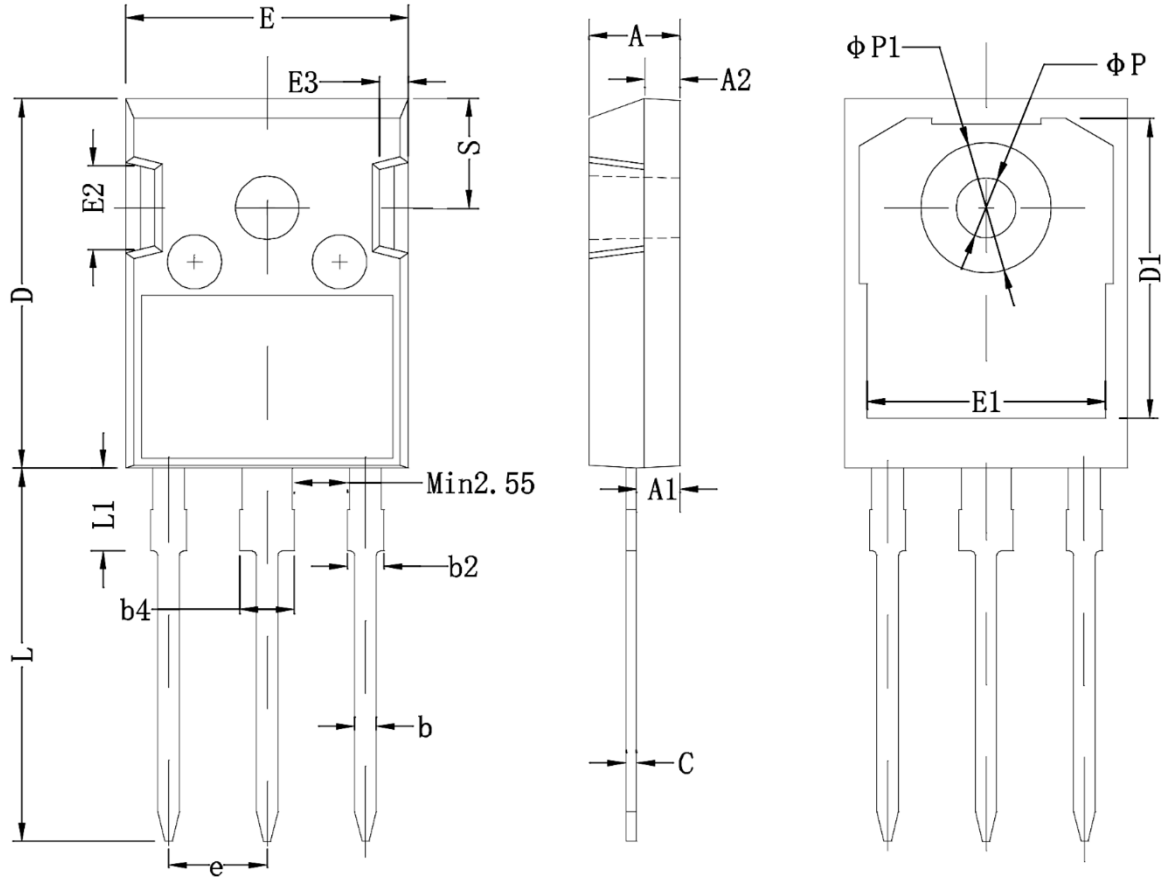


Fig.10 Transient Thermal Resistance

Product Dimension (TO-247-3L)



Dim	Millimeters		Inches		Dim	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	4.80	5.20	0.189	0.205	E1	13.00	13.60	0.512	0.535
A1	2.21	2.59	0.087	0.102	E2	4.80	5.20	0.189	0.205
A2	1.85	2.15	0.073	0.085	E3	2.30	2.70	0.091	0.106
b	1.11	1.36	0.044	0.054	e	5.44 BSC.		0.214 BSC.	
b2	1.91	2.21	0.075	0.087	L	19.82	20.22	0.780	0.796
b4	2.91	3.21	0.115	0.126	L1	-	4.30	-	0.169
c	0.51	0.75	0.020	0.030	φP	3.40	3.80	0.134	0.150
D	20.80	21.30	0.819	0.839	φP1	-	7.30	-	0.287
D1	16.25	16.85	0.640	0.663	S	6.15 BSC.		0.242 BSC.	
E	15.50	16.10	0.610	0.634					

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